



PMEG040V030EPD

40 V, 3 A low VF MEGA Schottky barrier rectifier

26 July 2016

Product data sheet

1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a CFP15 (SOT1289) power and flat lead Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Average forward current: $I_{F(AV)} \leq 3$ A
- Reverse voltage: $V_R \leq 40$ V
- Extremely low forward voltage
- High power capability due to clip-bonding technology and heat sink
- Small and thin SMD power plastic package, typical height 0.78 mm
- AEC-Q101 qualified

3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Freewheeling application
- Reverse polarity protection
- Low power consumption application

4. Quick reference data

Table 1. Quick reference data

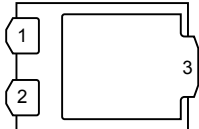
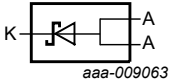
| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|-------------|-------------------------|--|-----|-----|-----|-----|---------|
| $I_{F(AV)}$ | average forward current | square wave; $\delta = 0.5$; $f = 20$ kHz; $T_{sp} \leq 167$ °C | | - | - | 3 | A |
| V_R | reverse voltage | $T_j = 25$ °C | | - | - | 40 | V |
| V_F | forward voltage | $I_F = 3$ A; $t_p \leq 300$ μ s; $\delta \leq 0.02$; $T_j = 25$ °C | | - | 425 | 490 | mV |
| I_R | reverse current | $V_R = 10$ V; $T_j = 25$ °C; pulsed; pulsed | [1] | - | 6 | 52 | μ A |
| | | $V_R = 40$ V; $T_j = 25$ °C; pulsed | [1] | - | 32 | 120 | μ A |

[1] Very short test pulse to prevent junction self heating



5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--|---|
| 1 | A | anode |  CFP15 (SOT1289) |  aaa-009063 |
| 2 | A | anode | | |
| 3 | K | cathode | | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|----------------|---------|---|---------|
| | Name | Description | Version |
| PMEG040V030EPD | CFP15 | plastic, thermal enhanced ultra thin SMD package; 3 leads; body: 5.8 x 4.3 x 0.78 mm | SOT1289 |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|----------------|--------------|
| PMEG040V030EPD | 040V U03E |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|-------------|-------------------------------------|---|-----|-----|------|--------------------|
| V_R | reverse voltage | $T_j = 25\text{ }^{\circ}\text{C}$ | | - | 40 | V |
| I_F | forward current | $T_{sp} \leq 165\text{ }^{\circ}\text{C}$; $\delta = 1$ | | - | 4.2 | A |
| $I_{F(AV)}$ | average forward current | square wave; $\delta = 0.5$; $f = 20\text{ kHz}$; $T_{sp} \leq 167\text{ }^{\circ}\text{C}$ | | - | 3 | A |
| I_{FSM} | non-repetitive peak forward current | square wave; $t_p = 8\text{ ms}$; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$ | | - | 120 | A |
| P_{tot} | total power dissipation | $T_{amb} \leq 25\text{ }^{\circ}\text{C}$ | [1] | - | 1.66 | W |
| | | | [2] | - | 2.15 | W |
| T_j | junction temperature | | | - | 175 | $^{\circ}\text{C}$ |
| T_{amb} | ambient temperature | | | -55 | 175 | $^{\circ}\text{C}$ |
| T_{stg} | storage temperature | | | -65 | 175 | $^{\circ}\text{C}$ |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm^2 .

9. Thermal characteristics

Table 6. Thermal characteristics

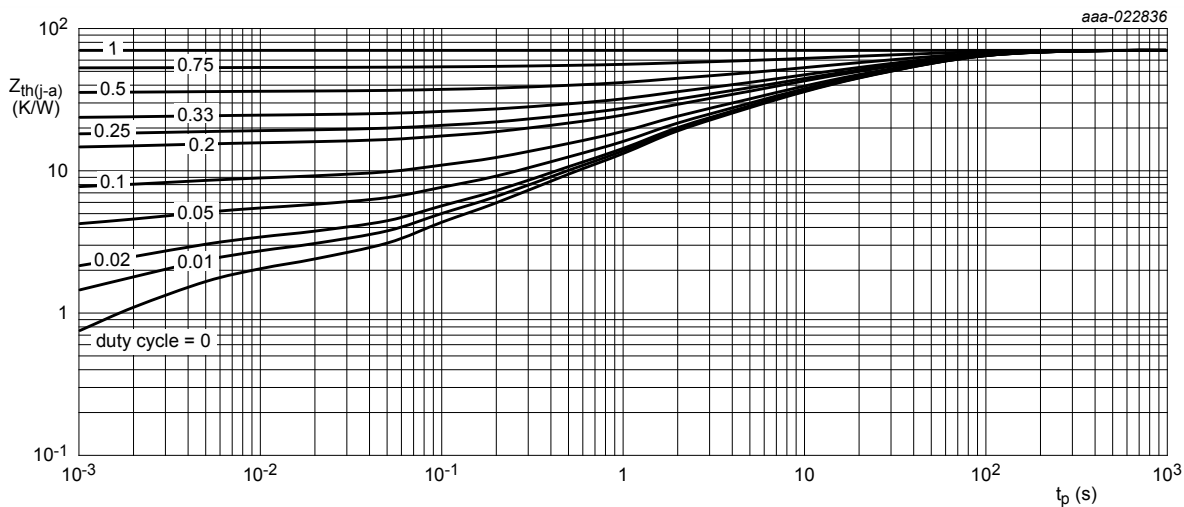
| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|----------------|--|-------------|--------|-----|-----|-----|------|
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | [1][2] | - | - | 90 | K/W |
| | | | [1][3] | - | - | 70 | K/W |
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point | | [4] | - | - | 3 | K/W |

[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

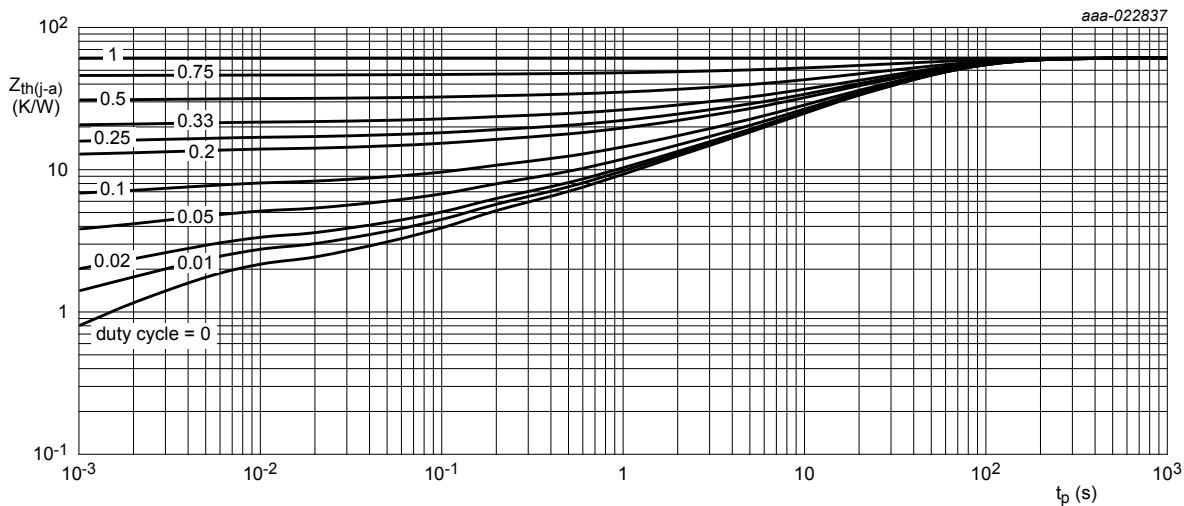
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm^2 .

[4] Soldering point of cathode tab.



FR4 PCB, standard footprint

Fig. 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for cathode 1 cm²

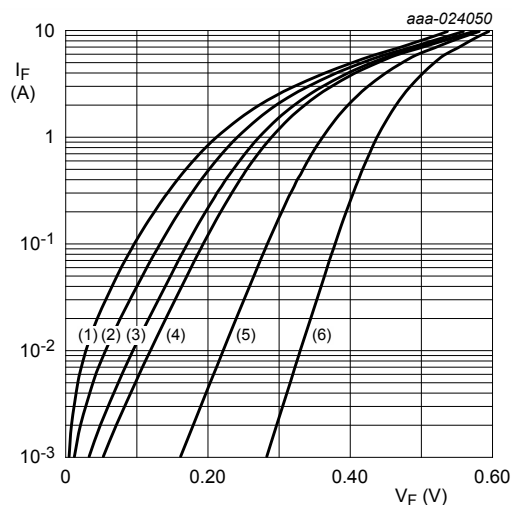
Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|-------------|--|---|-----|-----|-----|-----|---------------|
| $V_{(BR)R}$ | reverse breakdown voltage | $I_R = 3 \text{ mA}$; $T_j = 25 \text{ }^\circ\text{C}$; pulsed | [1] | 40 | - | - | V |
| V_F | forward voltage | $I_F = 0.1 \text{ A}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_j = 25 \text{ }^\circ\text{C}$ | | - | 285 | 320 | mV |
| | | $I_F = 1 \text{ A}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_j = 25 \text{ }^\circ\text{C}$ | | - | 360 | 420 | mV |
| | | $I_F = 1.5 \text{ A}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_j = 25 \text{ }^\circ\text{C}$ | | - | 380 | 435 | mV |
| | | $I_F = 2 \text{ A}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_j = 25 \text{ }^\circ\text{C}$ | | - | 395 | - | mV |
| | | $I_F = 3 \text{ A}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_j = 25 \text{ }^\circ\text{C}$ | | - | 425 | 490 | mV |
| | | $I_F = 3 \text{ A}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_j = -40 \text{ }^\circ\text{C}$ | | - | 485 | - | mV |
| | | $I_F = 3 \text{ A}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_j = 125 \text{ }^\circ\text{C}$ | | - | 340 | - | mV |
| I_R | reverse current | $V_R = 10 \text{ V}$; $T_j = 25 \text{ }^\circ\text{C}$; pulsed; pulsed | [1] | - | 6 | 52 | μA |
| | | $V_R = 30 \text{ V}$; $T_j = 25 \text{ }^\circ\text{C}$; pulsed | [1] | - | 17 | - | μA |
| | | $V_R = 40 \text{ V}$; $T_j = 25 \text{ }^\circ\text{C}$; pulsed | [1] | - | 32 | 120 | μA |
| | | $V_R = 40 \text{ V}$; $T_j = 125 \text{ }^\circ\text{C}$; pulsed | [1] | - | 18 | - | mA |
| C_d | diode capacitance | $V_R = 1 \text{ V}$; $f = 1 \text{ MHz}$; $T_j = 25 \text{ }^\circ\text{C}$ | | - | 395 | - | pF |
| | | $V_R = 4 \text{ V}$; $f = 1 \text{ MHz}$; $T_j = 25 \text{ }^\circ\text{C}$ | | - | 210 | - | pF |
| | | $V_R = 10 \text{ V}$; $f = 1 \text{ MHz}$; $T_j = 25 \text{ }^\circ\text{C}$ | | - | 130 | - | pF |
| t_{rr} | reverse recovery time step recovery | $I_F = 0.5 \text{ A}$; $I_R = 0.5 \text{ A}$; $I_{R(\text{meas})} = 0.1 \text{ A}$; $T_j = 25 \text{ }^\circ\text{C}$ | | - | 13 | - | ns |
| | reverse recovery time ramp recovery | $dI_F/dt = 200 \text{ A}/\mu\text{s}$; $T_j = 25 \text{ }^\circ\text{C}$; $I_F = 6 \text{ A}$; $V_R = 26 \text{ V}$ | | - | 11 | - | ns |

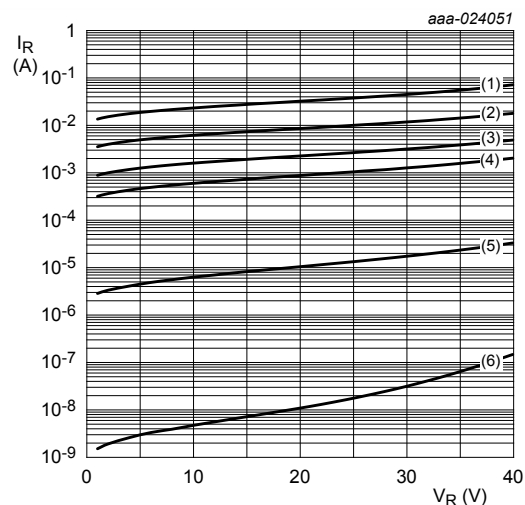
[1] Very short test pulse to prevent junction self heating



pulsed condition

- (1) $T_j = 150\text{ }^{\circ}\text{C}$
- (2) $T_j = 125\text{ }^{\circ}\text{C}$
- (3) $T_j = 100\text{ }^{\circ}\text{C}$
- (4) $T_j = 85\text{ }^{\circ}\text{C}$
- (5) $T_j = 25\text{ }^{\circ}\text{C}$
- (6) $T_j = -40\text{ }^{\circ}\text{C}$

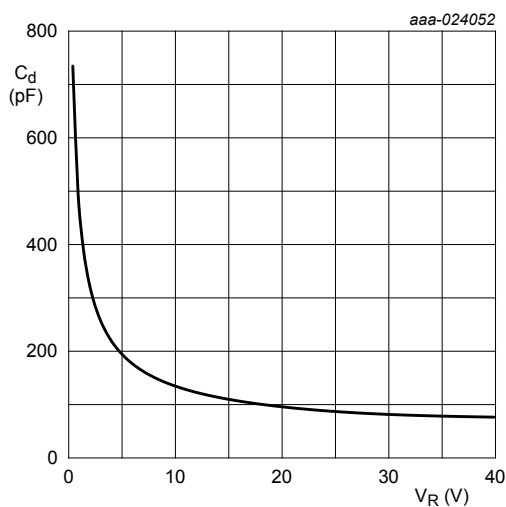
Fig. 3. Forward current as a function of forward voltage; typical values



pulsed condition

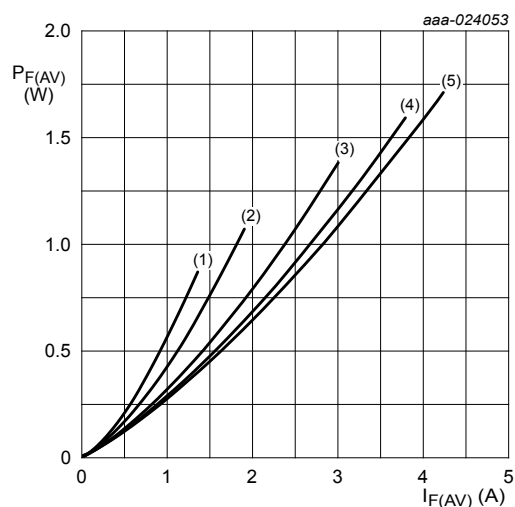
- (1) $T_j = 150\text{ }^{\circ}\text{C}$
- (2) $T_j = 125\text{ }^{\circ}\text{C}$
- (3) $T_j = 100\text{ }^{\circ}\text{C}$
- (4) $T_j = 85\text{ }^{\circ}\text{C}$
- (5) $T_j = 25\text{ }^{\circ}\text{C}$
- (6) $T_j = -40\text{ }^{\circ}\text{C}$

Fig. 4. Reverse current as a function of reverse voltage; typical values



$f = 1\text{ MHz}$; $T_{\text{amb}} = 25\text{ }^{\circ}\text{C}$

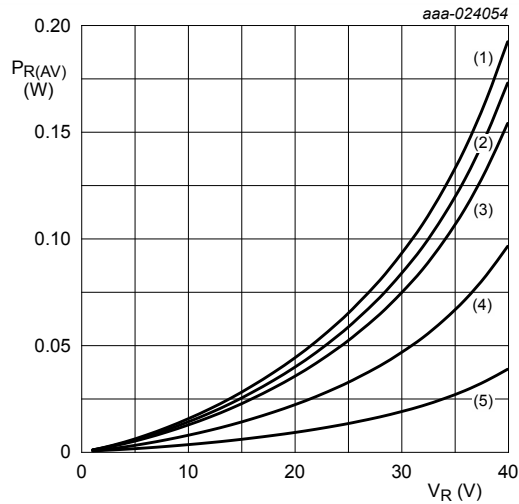
Fig. 5. Diode capacitance as a function of reverse voltage; typical values



$T_j = 100\text{ }^{\circ}\text{C}$

- (1) $\delta = 0.1$
- (2) $\delta = 0.2$
- (3) $\delta = 0.5$
- (4) $\delta = 0.8$
- (5) $\delta = 1$

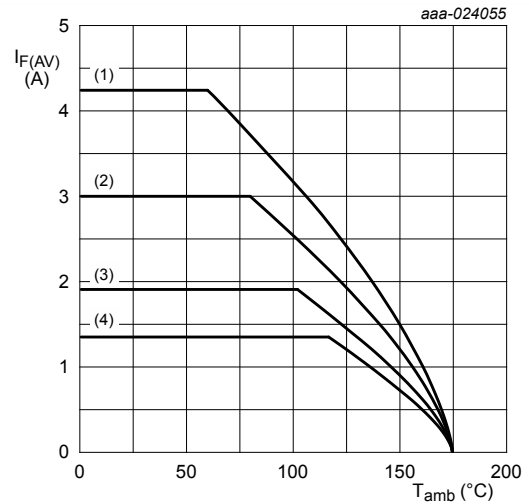
Fig. 6. Average forward power dissipation as a function of average forward current; typical values



$T_j = 100\text{ }^{\circ}\text{C}$

- (1) $\delta = 1$
- (2) $\delta = 0.9$
- (3) $\delta = 0.8$
- (4) $\delta = 0.5$
- (5) $\delta = 0.2$

Fig. 7. Average reverse power dissipation as a function of reverse voltage; typical values

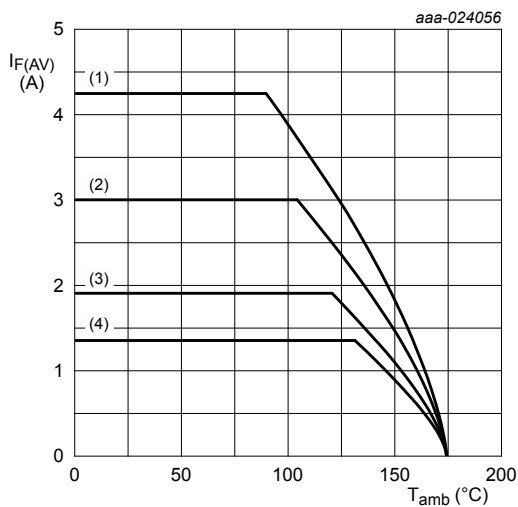


FR4 PCB, standard footprint

$T_j = 175\text{ }^{\circ}\text{C}$

- (1) $\delta = 1$; DC
- (2) $\delta = 0.5$; $f = 20\text{ kHz}$
- (3) $\delta = 0.2$; $f = 20\text{ kHz}$
- (4) $\delta = 0.1$; $f = 20\text{ kHz}$

Fig. 8. Average forward current as a function of ambient temperature; typical values

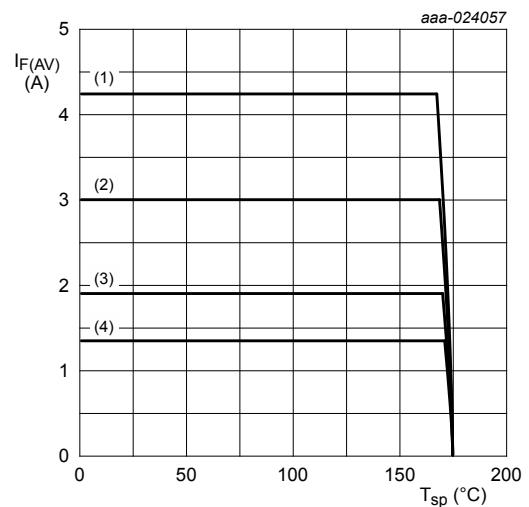


FR4 PCB, mounting pad for cathode 1 cm^2

$T_j = 175\text{ }^{\circ}\text{C}$

- (1) $\delta = 1$; DC
- (2) $\delta = 0.5$; $f = 20\text{ kHz}$
- (3) $\delta = 0.2$; $f = 20\text{ kHz}$
- (4) $\delta = 0.1$; $f = 20\text{ kHz}$

Fig. 9. Average forward current as a function of ambient temperature; typical values



$T_j = 175\text{ }^{\circ}\text{C}$

- (1) $\delta = 1$; DC
- (2) $\delta = 0.5$; $f = 20\text{ kHz}$
- (3) $\delta = 0.2$; $f = 20\text{ kHz}$
- (4) $\delta = 0.1$; $f = 20\text{ kHz}$

Fig. 10. Average forward current as a function of solder point temperature; typical values

11. Test information

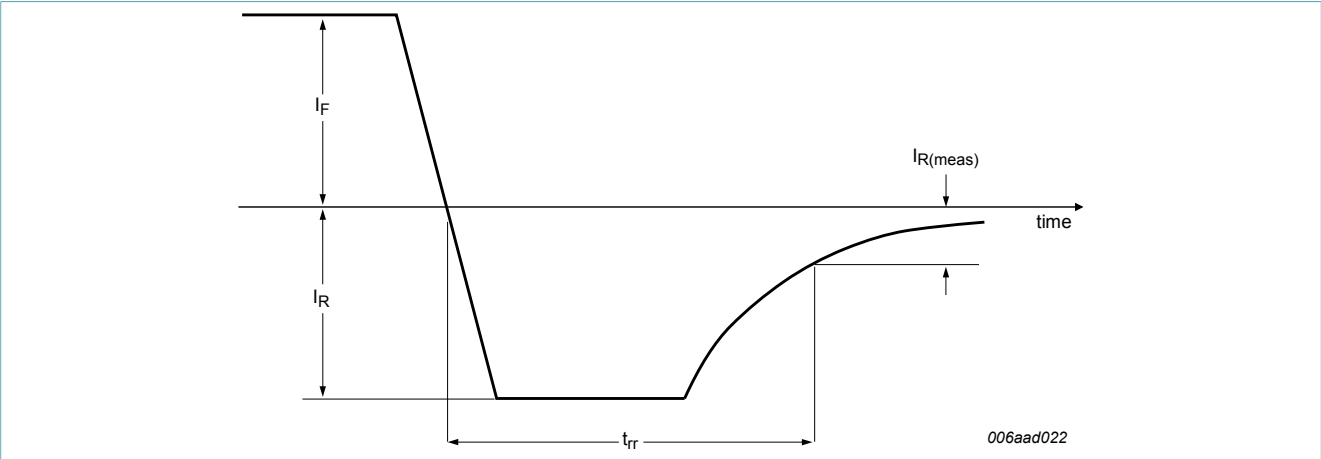


Fig. 11. Reverse recovery definition; step recovery

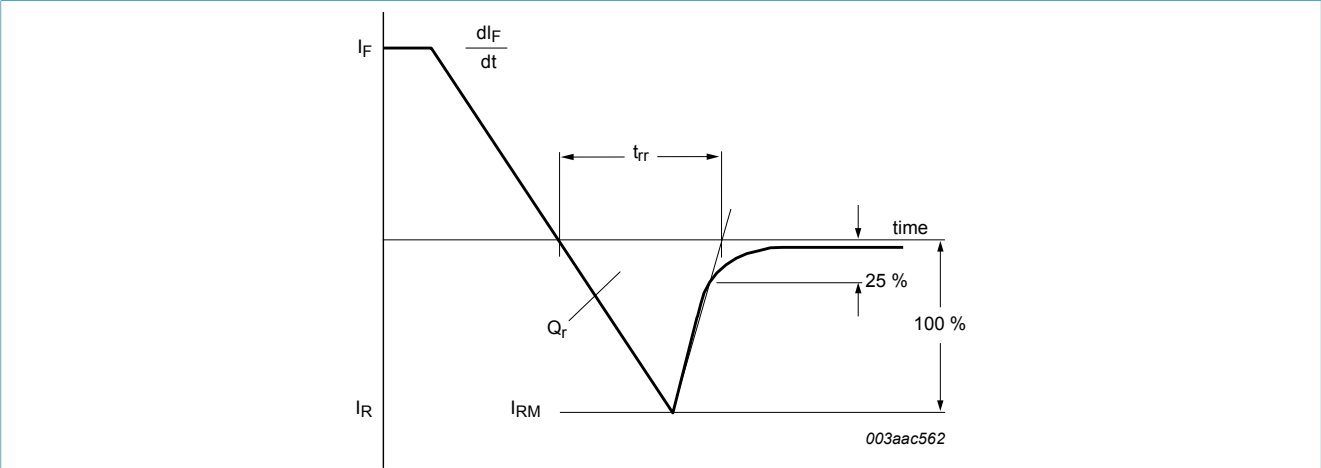


Fig. 12. Reverse recovery definition; ramp recovery

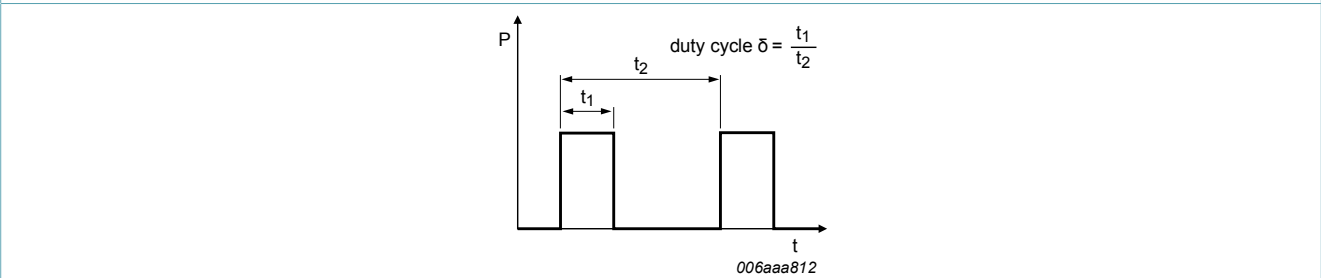


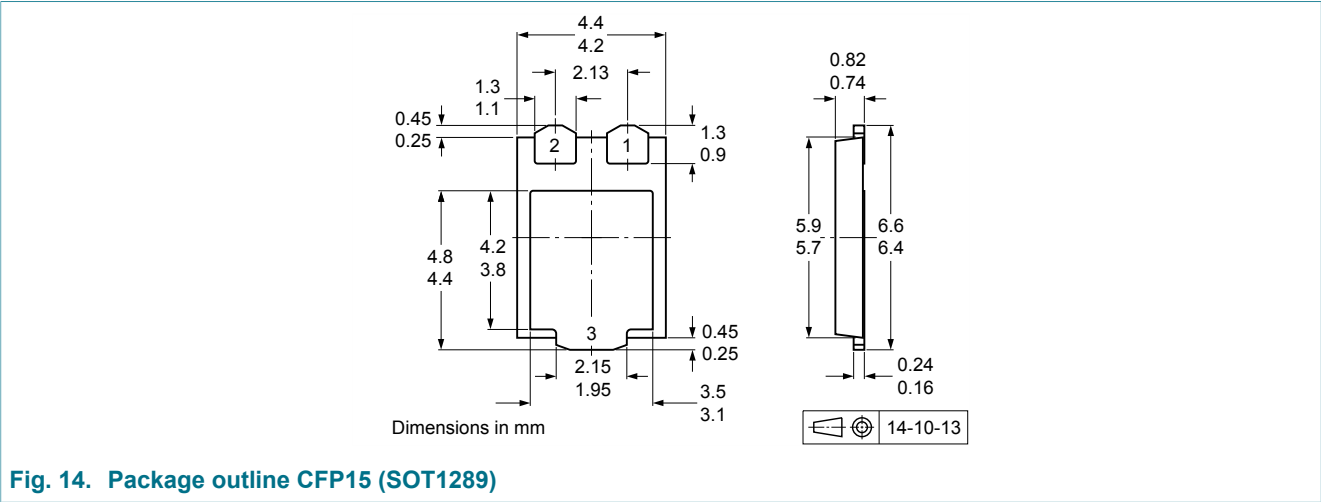
Fig. 13. Duty cycle definition

The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

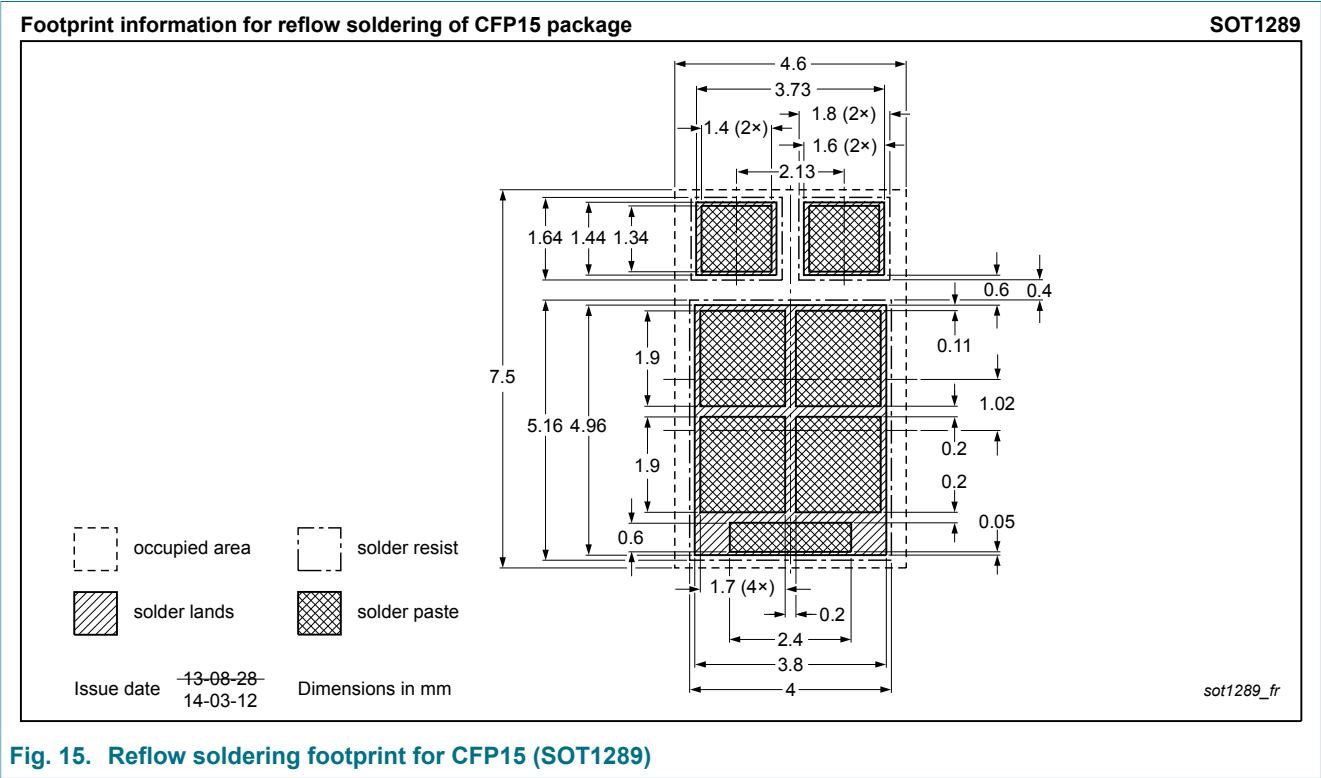
Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



13. Soldering



14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
|--------------------|--------------|--------------------|---------------|------------|
| PMEG040V030EPD v.1 | 20160726 | Product data sheet | - | - |

15. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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